

PNP SILICON LOW POWER TRANSISTOR

Qualified per MIL-PRF-19500/354

Devices

2N2604

2N2605

Qualified Level

JAN, JANTX
JANTXV

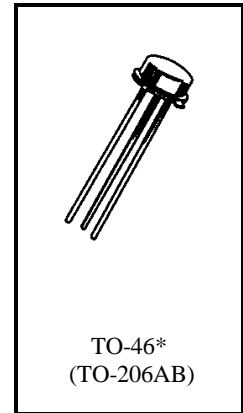
MAXIMUM RATINGS

Ratings	Symbol	2N2604	2N2605	Units
Collector-Base Voltage	V_{CBO}	80	70	Vdc
Collector-Emitter Voltage	V_{CEO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	6.0		Vdc
Collector Current	I_C	30		mAdc
Total Power Dissipation @ $T_A = +25^{\circ}C^{(1)}$	P_T	400		mW/ $^{\circ}C$
Operating & Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200		$^{\circ}C$

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max.	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.437	$^{\circ}C/mW$

1) Derate linearly 2.28 mW/ $^{\circ}C$ above $T_A = +25^{\circ}C$



*See appendix A for package outline

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
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OFF CHARACTERISTICS

Collector-Base Breakdown Voltage $I_C = 10 \mu A_{dc}$	2N2604 2N2605	$V_{(BR)CBO}$	80 70	Vdc
Collector-Emitter Breakdown Voltage $I_C = 10 mAdc$		$V_{(BR)CEO}$	60	Vdc
Emitter-Base Breakdown Current $I_E = 10 \mu A_{dc}$		$V_{(BR)EBO}$	6.0	Vdc
Collector-Base Cutoff Current $V_{CB} = 50 Vdc$		I_{CBO}	10	ηA_{dc}
Emitter-Base Cutoff Current $V_{EB} = 5.0 Vdc$		I_{EBO}	2.0	ηA_{dc}
Collector-Emitter Cutoff Current $V_{CE} = 50 Vdc$		I_{CES}	10	ηA_{dc}

2N2604, 2N2605 JAN SERIES

ELECTRICAL CHARACTERISTICS (con't)

Characteristics	Symbol	Min.	Max.	Unit
ON CHARACTERISTICS (2)				
Forward-Current Transfer Ratio $I_C = 10 \mu\text{A}_{dc}, V_{CE} = 5.0 \text{ V}_{dc}$ 2N2604 2N2605	h_{FE}	40	120	
$I_C = 500 \mu\text{A}_{dc}, V_{CE} = 5.0 \text{ V}_{dc}$ 2N2604 2N2605		100	300	
$I_C = 10 \text{ mA}_{dc}, V_{CE} = 5.0 \text{ V}_{dc}$ 2N2604		60	180	
2N2605		150	450	
$I_C = 10 \text{ mA}_{dc}, V_{CE} = 5.0 \text{ V}_{dc}$ 2N2604 2N2605		40	160	
		100	400	
Collector-Emitter Saturation Voltage $I_C = 10 \text{ mA}_{dc}, I_B = 500 \mu\text{A}_{dc}$	$V_{CE(sat)}$		0.3	Vdc
Base-Emitter Saturation Voltage $I_C = 10 \text{ mA}_{dc}, I_B = 500 \mu\text{A}_{dc}$	$V_{BE(sat)}$	0.7	0.9	Vdc

DYNAMIC CHARACTERISTICS

Small-Signal Short-Circuit Input Impedance $I_C = 1.0 \text{ mA}_{dc}, V_{CB} = 5.0 \text{ V}_{dc}, f = 1.0 \text{ kHz}$ 2N2604 2N2605	h_{ie}	1.0 2.0	10 20	$k\Omega$
Small-Signal Open-Circuit Output Admittance $I_C = 1.0 \text{ mA}_{dc}, V_{CE} = 5.0 \text{ V}_{dc}, f = 1.0 \text{ kHz}$ 2N2604 2N2605	h_{oe}		40 60	μmhos
Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = 1.0 \text{ mA}_{dc}, V_{CE} = 5.0 \text{ V}_{dc}, f = 1.0 \text{ kHz}$ 2N2604 2N2605	h_{fe}	60 150	180 450	
Magnitude of Small-Signal Forward Current Transfer Ratio $I_C = 0.5 \text{ mA}_{dc}, V_{CE} = 5.0 \text{ V}_{dc}, f = 30 \text{ MHz}$	$ h_{fe} $	1.0	8.0	
Output Capacitance $V_{CB} = 5.0 \text{ V}_{dc}, I_E = 0, 100 \text{ kHz} \leq f \leq 1.0 \text{ MHz}$	C_{obo}		6.0	pF
Noise Figure $V_{CE} = 5.0 \text{ V}_{dc}, I_C = 10 \mu\text{A}_{dc}, R_g = 10 k\Omega, f = 100 \text{ Hz}$ $V_{CE} = 5.0 \text{ V}_{dc}, I_C = 10 \mu\text{A}_{dc}, R_g = 10 k\Omega, f = 1.0 \text{ kHz}$ $V_{CE} = 5.0 \text{ V}_{dc}, I_C = 10 \mu\text{A}_{dc}, R_g = 10 k\Omega, f = 10 \text{ kHz}$	F_1 F_2 F_3		5.0 3.0 3.0	dB

(2) Pulse Test: Pulse Width = 300 μs , Duty Cycle \leq 2.0%.